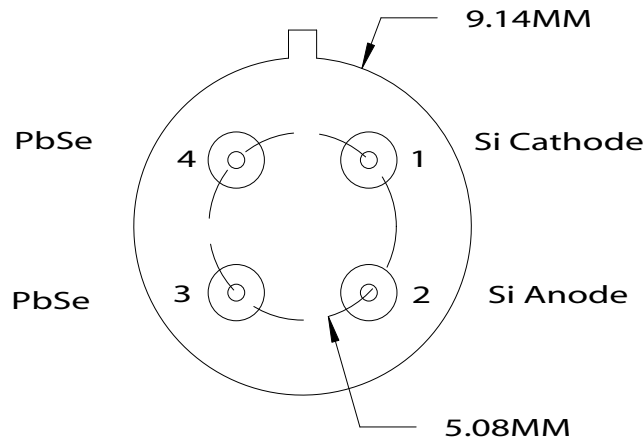


Si SPECIFICATIONS

TOP Si PV PHOTODIODE
 ACTIVE AREA - 3.5MM Dia
 WAVELENGTH - .3-1.1 μ
 SHUNT RESISTANCE - 1500M @10mV
 DARK CURRENT - 0.2nA @10V
 CAPACITANCE - 100pF @0V
 RESPONSIVITY - .65A/W @900nm
 NEP(W/Hz) - 1.3×10^{-14} @900nm
 TIME CONSTANT - 2000ns @0V



PbSe SPECIFICATIONS

BOTTOM PbSe PC DETECTOR
 ACTIVE AREA - 2MMX2MM
 WAVELENGTH - 1.0 - 4.7 μ
 RESISTANCE - .3-1.5 M ohms
 RESPONSIVITY - >3000V/W
 $D^*(Pk,1000,1) \times 10^{-2}$ 2.0
 TIME CONSTANT - 3 μ s

NOTE:

- All assemblies are hermetically sealed
- Custom filters are available
- Other active areas are available
- PbS and InGaAs materials are available

| | | | | | | | | |
|--|------------------|----|------|---|-----------------|-------|------|-----|
| DO NOT SCALE DRAWING | DRAWN | | DATE | N.E.P. NEW ENGLAND PHOTOCONDUCTOR | | | | |
| | CHECKED | | DATE | | | | | |
| | DESIGNER | GG | DATE | FS-2/2.5-5 | | | | |
| | ENGINEER | PB | DATE | | | | | |
| MATERIAL: | PROJECT ENGINEER | | DATE | | | | | |
| FINISH SPECS: | PROJECT APPROVAL | | DATE | SIZE | CODE IDENT. NO. | TYPE | 1489 | REV |
| | PMB 3/3/09 | | | A | | | | |
| SUNSTAR传感与控制 http://www.sensor-ic.com/ TEL:0755-83376549 FAX:0755-83376182 E-MAIL:szss20@163.com | | | | SCALE | none | SHEET | | 1 |